

# BTA316-600E

3Q Hi-Com Triac

Rev. 02 — 23 November 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series E" is intended for interfacing with low power drivers including microcontrollers.

### 1.2 Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

### 1.3 Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	-	600	V
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; see <a href="#">Figure 4</a> ; see <a href="#">Figure 5</a>	-	-	140	A
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 101\text{ °C}$ ; see <a href="#">Figure 3</a> ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 2</a>	-	-	16	A

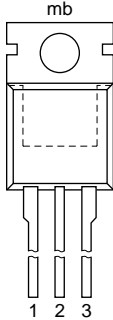



**Table 1. Quick reference data ...continued**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 7</a>	-	-	10	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 7</a>	-	-	10	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 7</a>	-	-	10	mA

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

**SOT78 (TO-220AB)**

## 3. Ordering information

**Table 3. Ordering information**

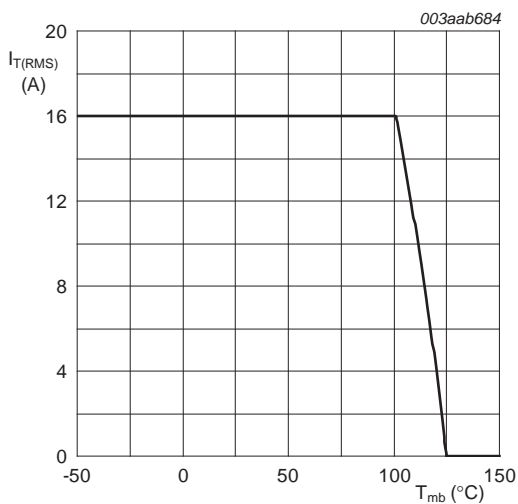
Type number	Package		Version
	Name	Description	
BTA316-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Limiting values

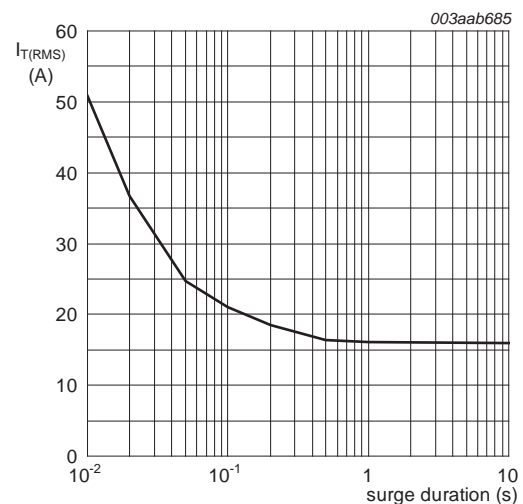
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 101\text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 3</a> ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 2</a>	-	16	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; see <a href="#">Figure 4</a> ; see <a href="#">Figure 5</a>	-	140	A
		full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 16.7\text{ ms}$	-	150	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	98	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_T = 20\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	$^{\circ}\text{C}$
$T_j$	junction temperature		-	125	$^{\circ}\text{C}$



**Fig 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{mb} = 101\text{ }^{\circ}\text{C}$

**Fig 2. RMS on-state current as a function of surge duration; maximum values**

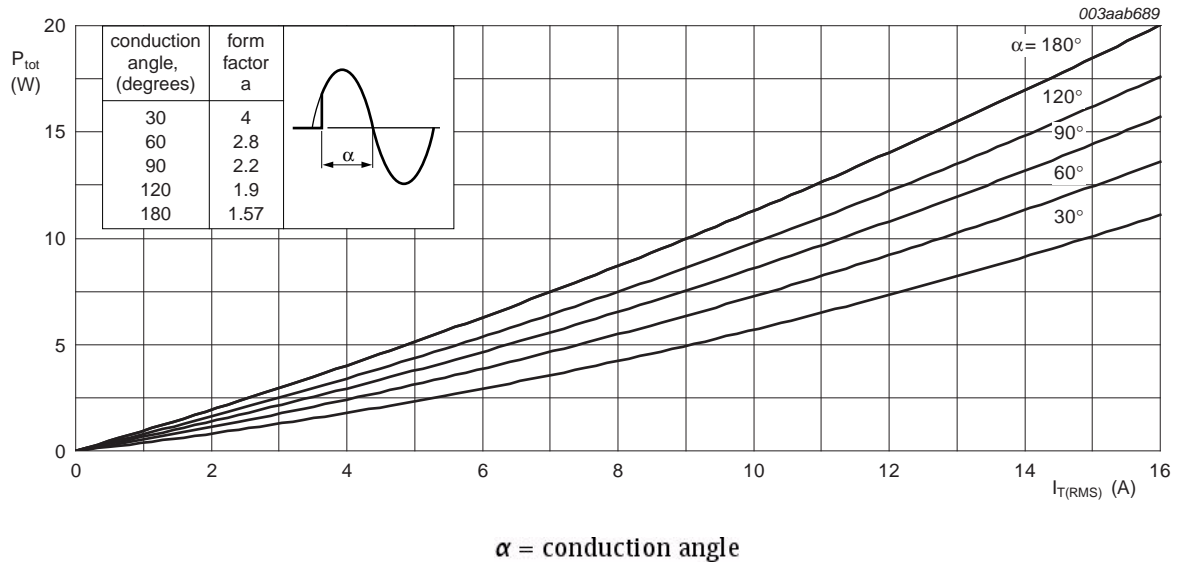


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

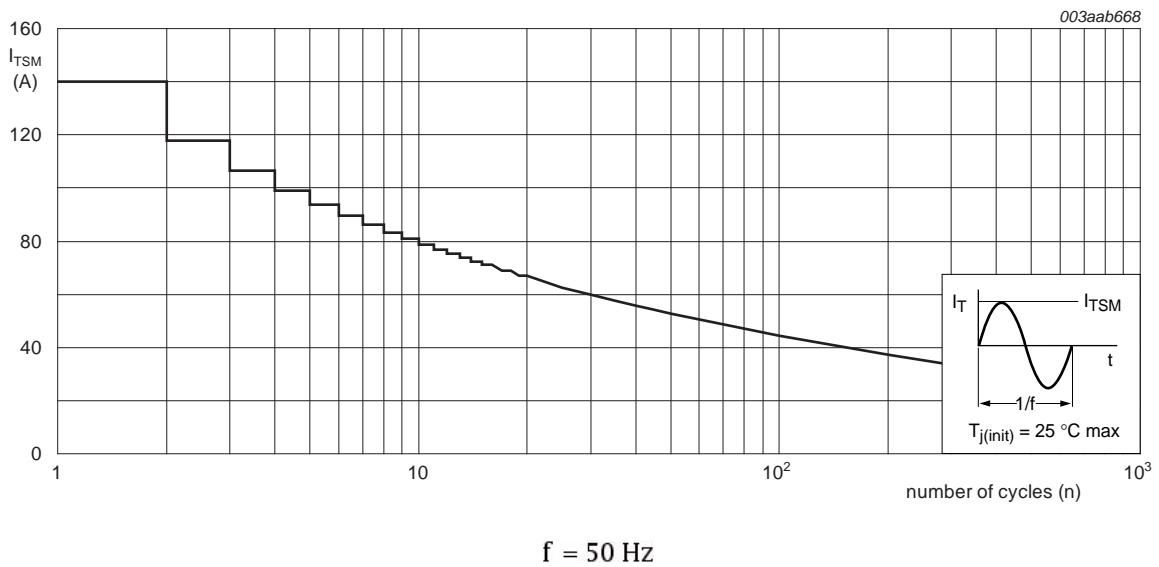
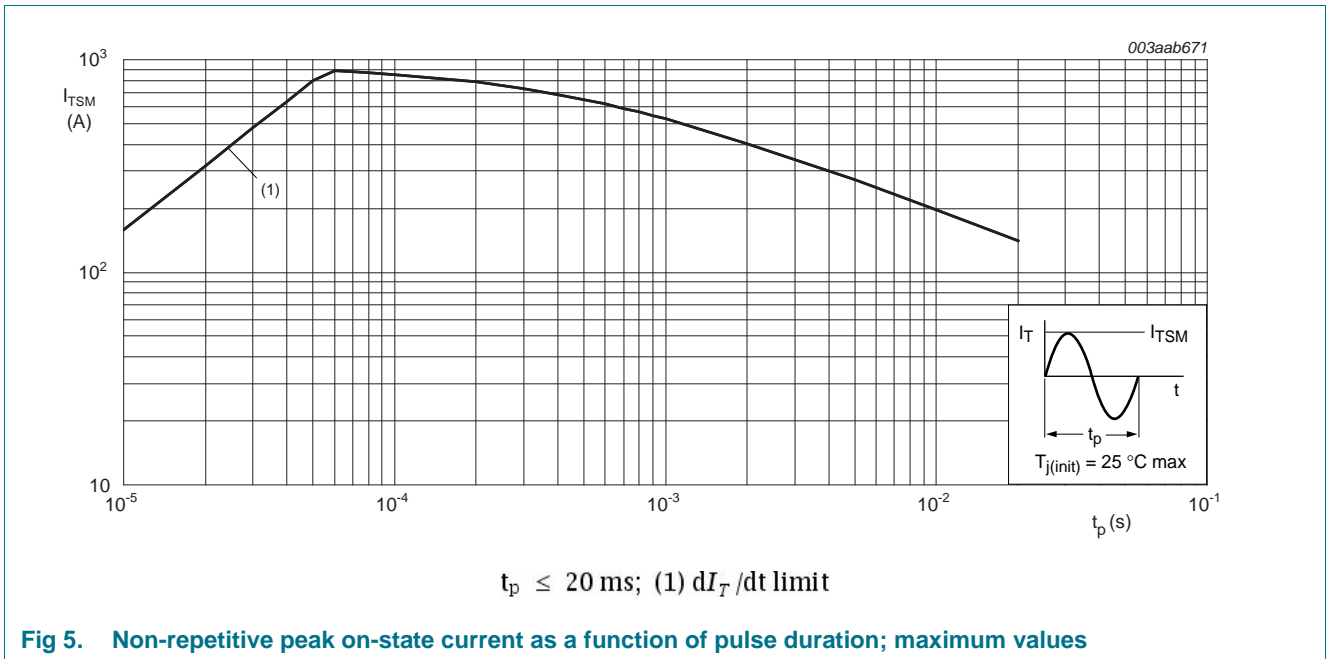


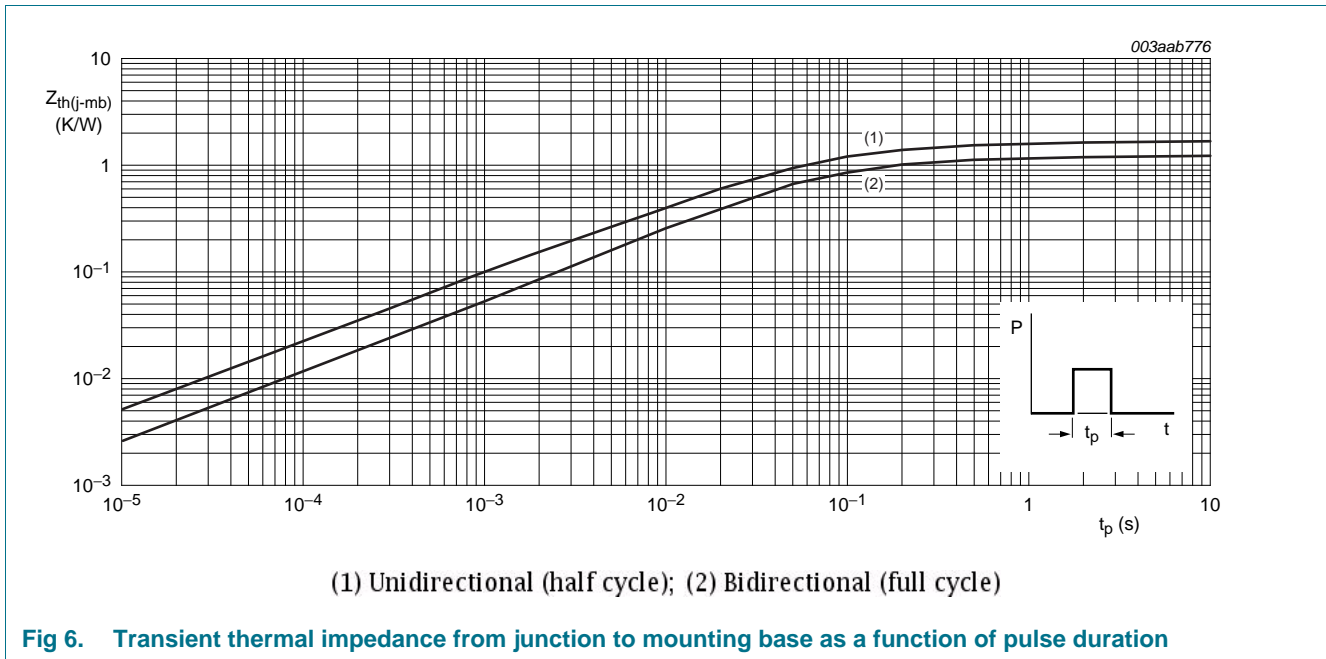
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



**5. Thermal characteristics**

**Table 5. Thermal characteristics**

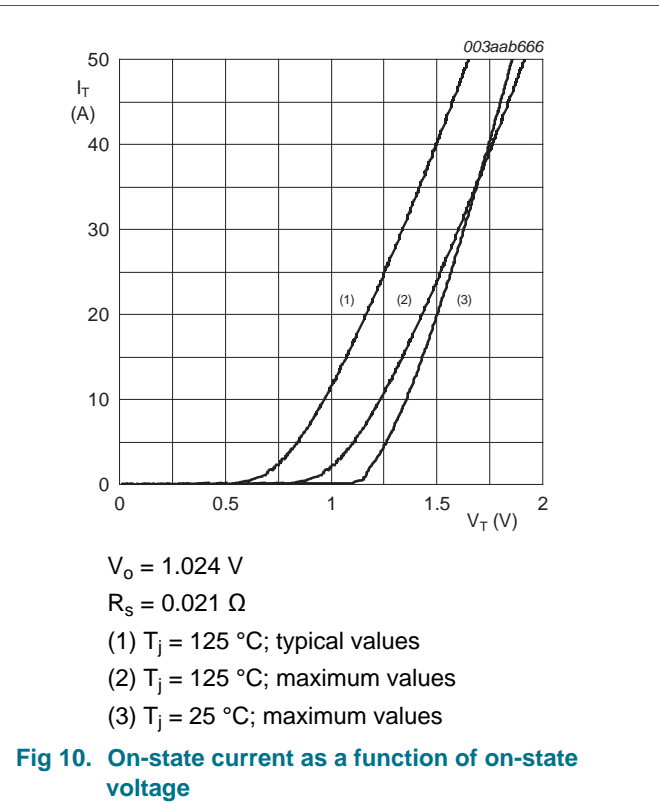
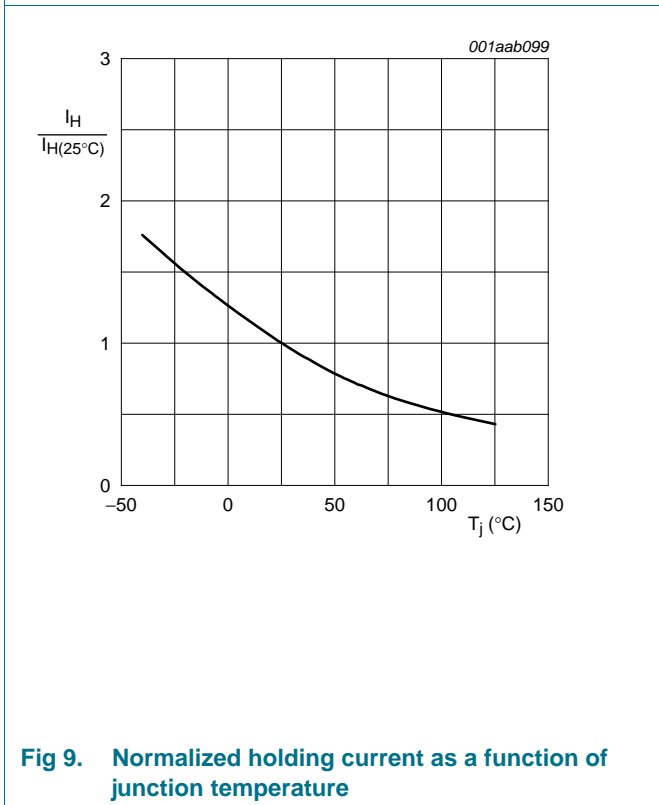
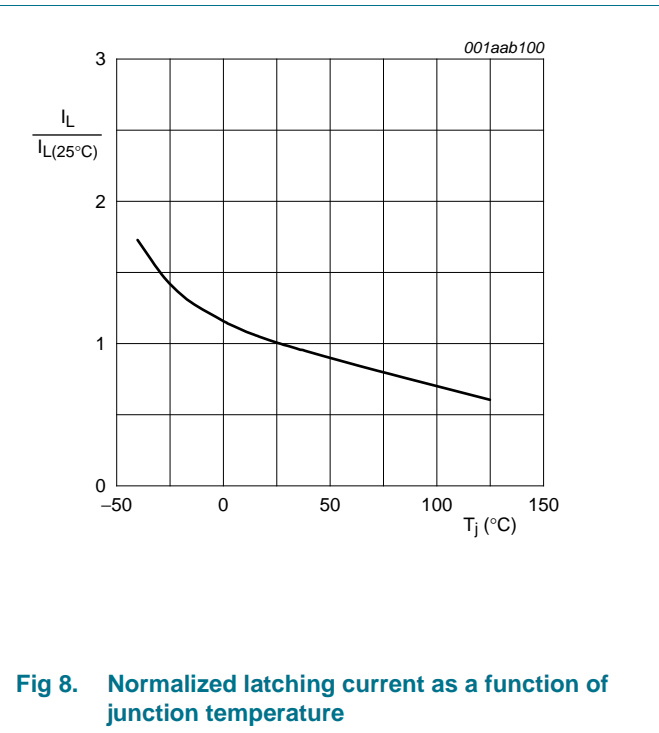
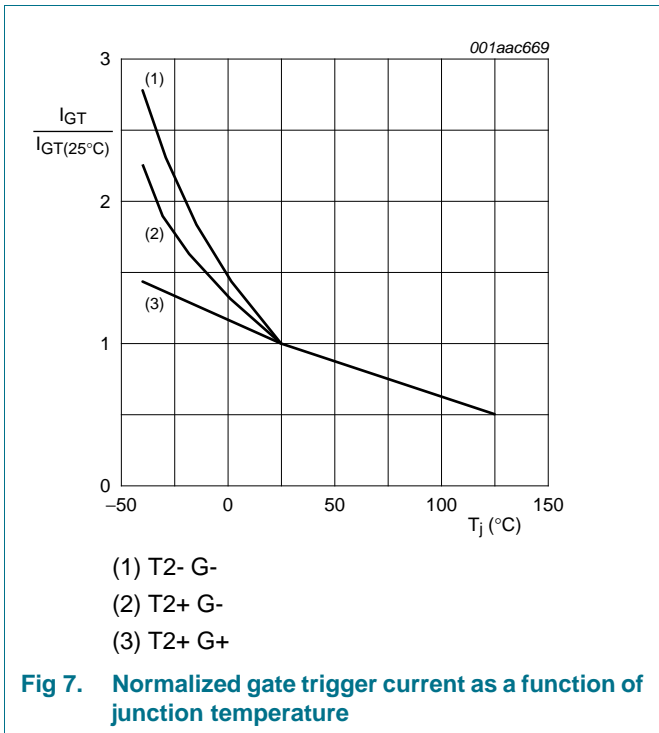
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; see <a href="#">Figure 6</a>	-	-	1.2	K/W
		half cycle; see <a href="#">Figure 6</a>	-	-	1.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 7</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 7</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 7</a>	-	-	10	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 8</a>	-	-	25	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 8</a>	-	-	30	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 8</a>	-	-	30	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 9</a>	-	-	15	mA
$V_T$	on-state voltage	$I_T = 18\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 10</a>	-	1.3	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 11</a>	-	0.8	1.5	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ °C}$ ; see <a href="#">Figure 11</a>	0.25	0.4	-	V
$I_D$	off-state current	$V_D = 600\text{ V}$ ; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ °C}$ ; exponential waveform; gate open circuit	60	-	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 16\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit	8	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 16\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; "without snubber" condition; gate open circuit	5	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 16\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit	12	-	-	A/ms
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 20\text{ A}$ ; $V_D = 600\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	$\mu$ s





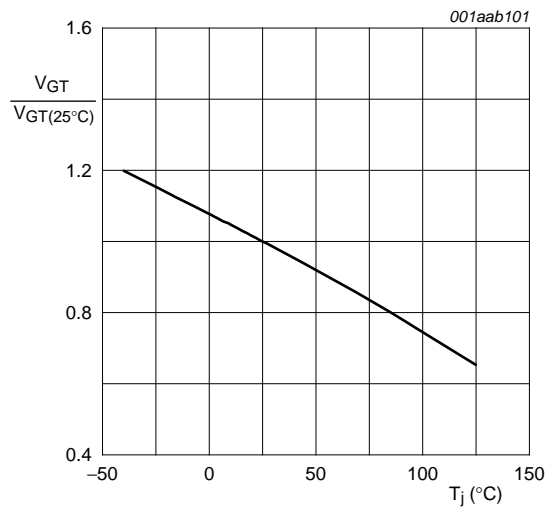


Fig 11. Normalized gate trigger voltage as a function of junction temperature

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

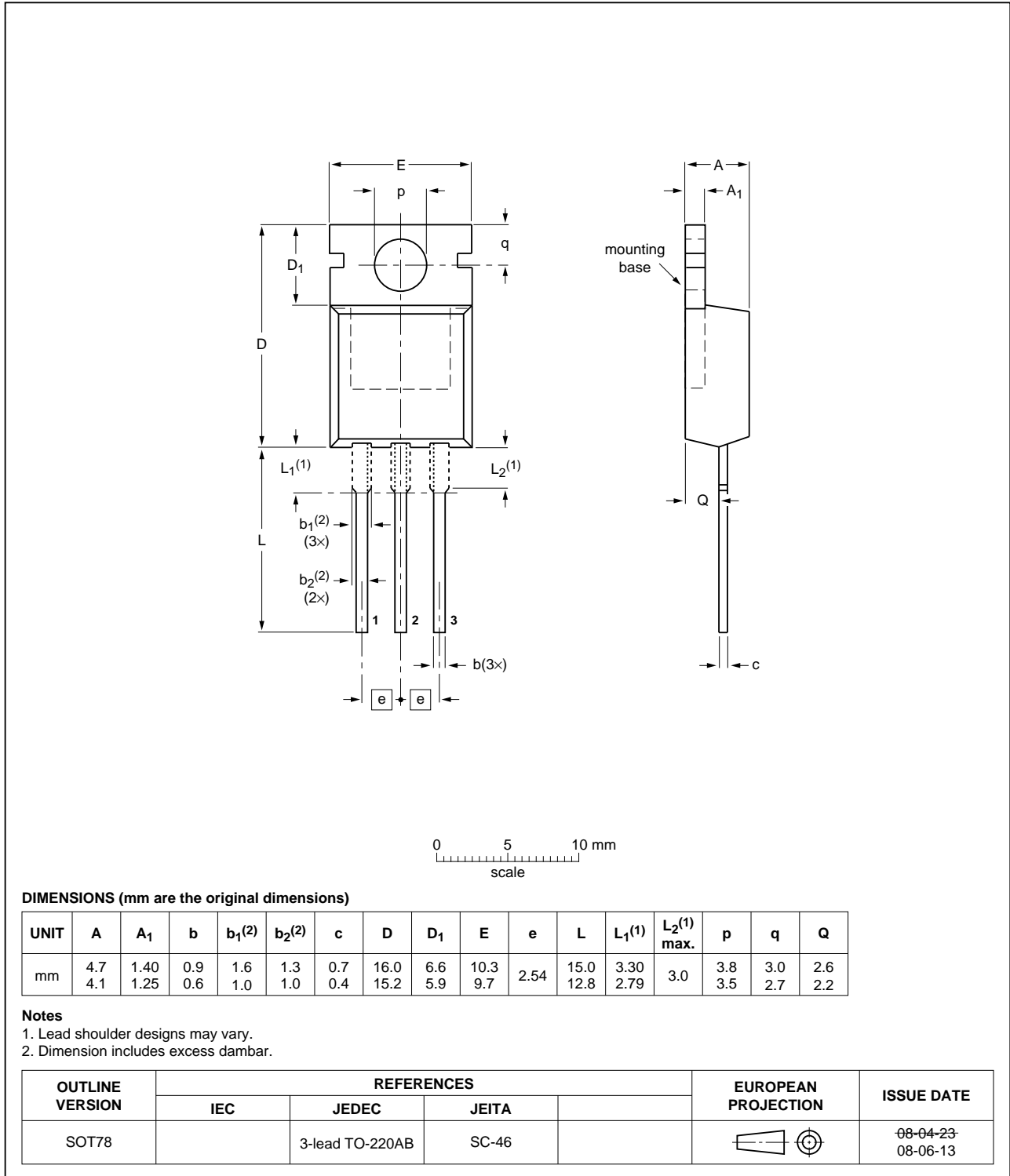


Fig 12. Package outline SOT78 (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA316-600E v.2	20101123	Product data sheet	-	BTA316_SER_D_E v.1
Modifications:	<ul style="list-style-type: none"><li>• Type number BTA316-600E separated from data sheet BTA316_SER_D_E v.1.</li><li>• Various changes to content.</li></ul>			
BTA316_SER_D_E v.1	20070418	Product data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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